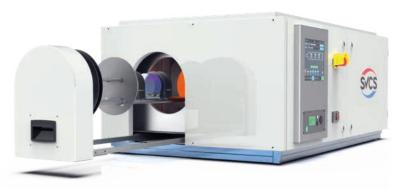


Horizontal Furnaces Reference Guide

Small Single Tube Furnace for R&D

- Ideally suited for R&D labs and pilot fabs Small footprint
- Table or standalone solution (with stands)
- Stackable desing (e.g. double tabletop variant)
- Low power consumption
- Easy operation and maintenance
- Heating element with 1 or 3 temperature zones and max. temperature up to 1300 °C
- Modern modular proprietary control system
- Up to 8 gas lines and 2 liquid sources
- Independent hardware safety interlocks
- Integration of vacuum pump systems
- in cooperation with leading pump manufacturers





Processes

Atmospheric

- Diffusion (drive-in) high temperature processes
- Doping from solid, liquid and gaseous dopant sources e.g. BBr₃, B₂H₆, POCL₃, PH₃, BN
- Various thermal processing e.g. annealing, curing, sintering
- Pyrogenic Wet Oxide with External Burning System
- Wet Oxide with ultra pure steamer
- Dry Oxide
- HiPOx (High Pressure Oxide)

LPCVD

- Silicon nitride
- Low temperature oxide (LTO)
- High temperature oxide (HTO)
- **TEOS** oxide
- Polysilicon, both with tilt and flat temperature profile
- Doped polysilicon
- Oxynitride

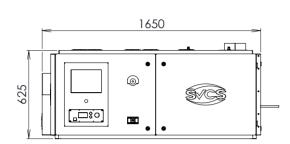
PECVD

Silicon nitride

(including anti-reflective SiN solar cell coating)

- Silicon oxide
- Oxinitride

DCE or HCl optional for all processes



Front views

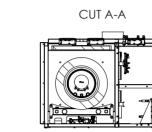
Side views

860

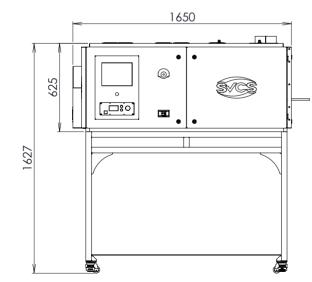
SVCS

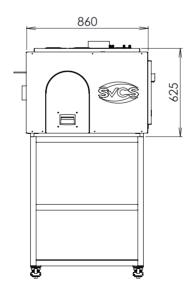
625

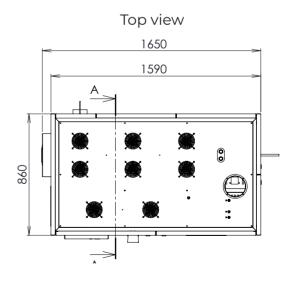
Cut view



Drawings with optional stands (mm)







Up to 4-position Furnace for Production

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SICS

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- Maintenance friendly mechanical design
- State of the art modular control system, in-house designed and manufactured
- 10,4" high-res touchscreen for operator interface
- Up to 4 stacked quartz or SiC tube reactor chambers for various procesess
- No thermal interference between different tubes
- Contactless fully automated boat-in-tube loading both cantilever or softlanding configurations
- Independent tube level control system

SICS

- HW safety interlocks independent on main CPU
- HEPA or ULPA filtres installed in load station
- Boat elevator and wafer handling automation
- UHP face seal fittings and welds for connections
- UHP orbital weldings made in 100/10 Cleanroom



Processes

Atmospheric

- Diffusion (drive-in) high temperature processes
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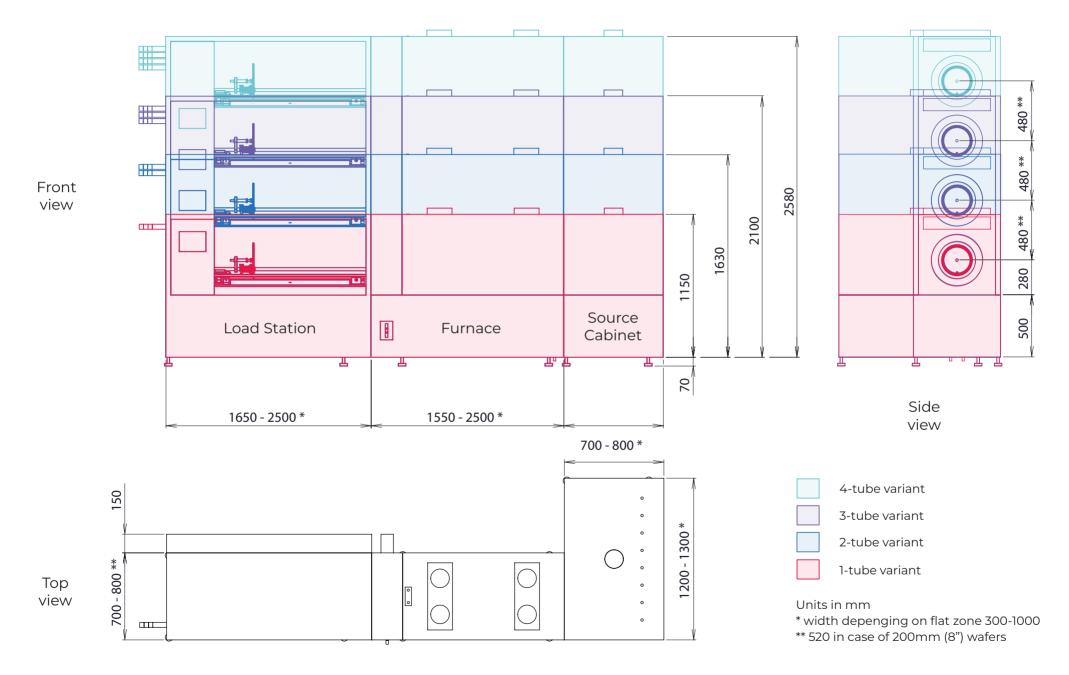
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PECVD

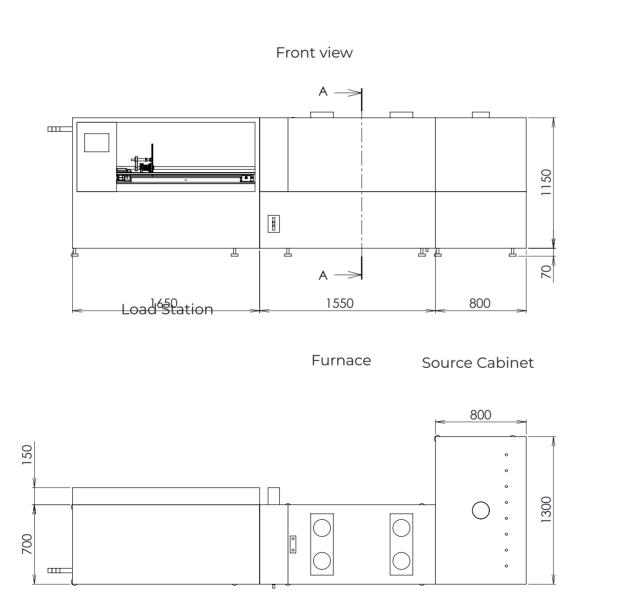
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- (including anti-reflective SiN solar cell coating)
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DCE or HCl optional for all processes

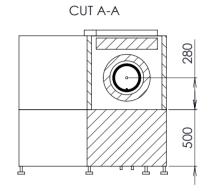
Basic size comparison of Horizontal Furnaces



1-Position Horizontal Furnace

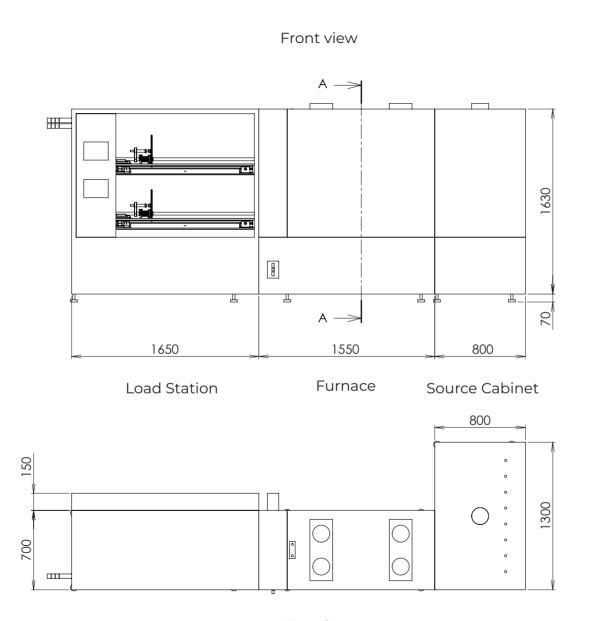


Side cut view

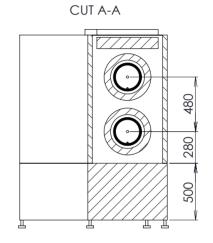


Top view

2-Position Horizontal Furnace

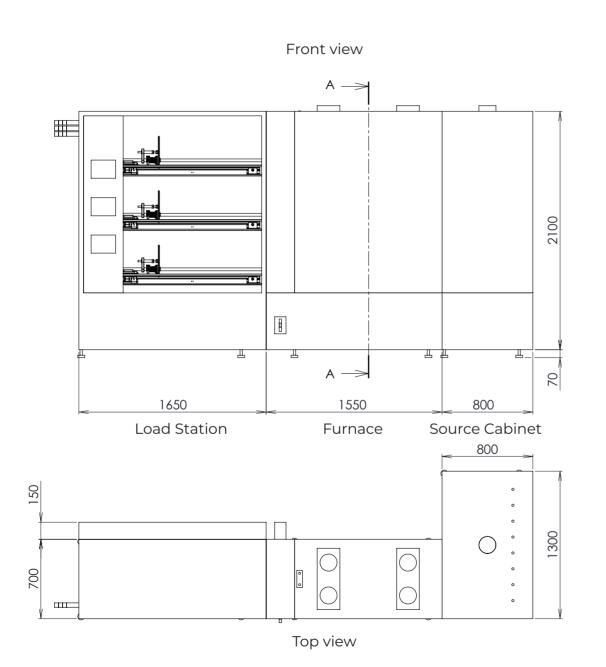


Side cut view



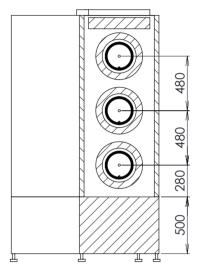


3-Position Horizontal Furnace

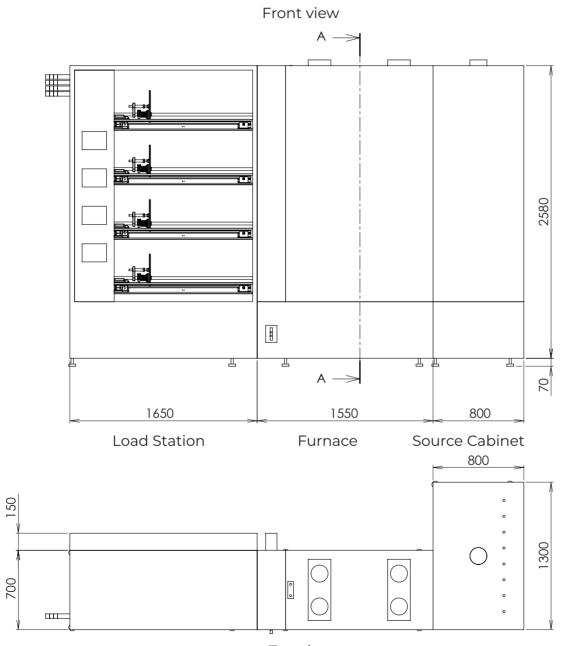


Side cut view





4-Position Horizontal Furnace



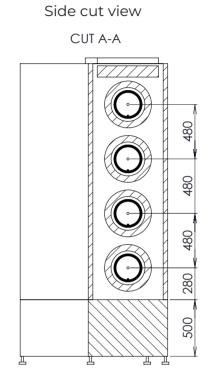




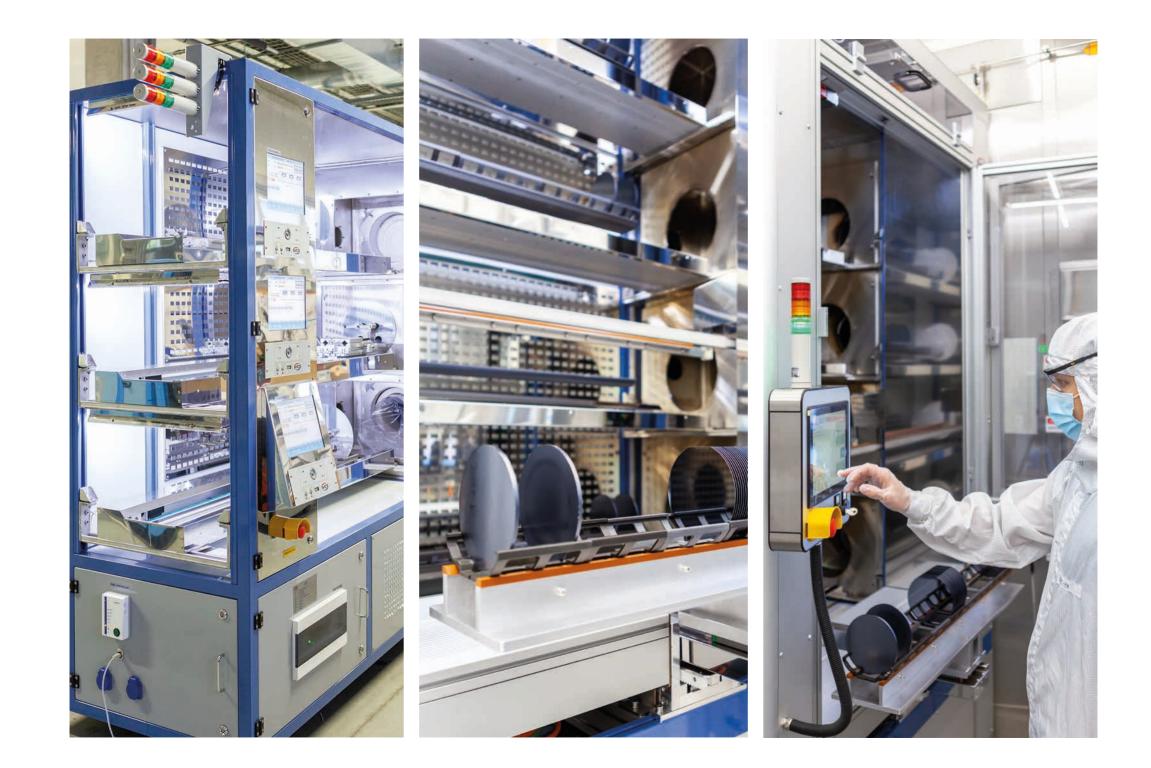
Table of properties

Tabletop

1-4 Position

Weight	ca. 350kg	n/a
Sample dimensions W x H x D (mm)	1650 x 625 x 860 (Without stands)	3900-5800 x 1150-2580 x 1200-1300 (Depending on configuration)
Wafer size	50 - 200 mm	50 - 200 mm
Wafer load	Up to 50 wafers *	Up to 300 per tube *
Heating system	l or 3 zones	3 or 5 zone
Flat zone	Up to 600 mm	300 - 1000 mm
Process temperature **	200°C to 1230°C	200°C to 1300°C
Power consumption	17kW	18kW - 30kW per tube
3-Phase Power supply ***	400/80VAC, 40 - 100A, 50/60Hz	150 mm: 400/480VAC, 140A, 50/60Hz 200 mm: 400/480VAC, 160A, 50/60Hz
Clean dry air	70 – 110 psig (4,8 to 7,6 bar)	70 – 110 psig (4,8 to 7,6 bar)
Cooling water	10 – 15 LPM	40 – 60 LPM
Exhaust	100m³/h	210m³/h per tube

* in case of reference 150mm (6") variant ** Accurancy ± 0.5°C across flat zone *** Adapted to power grid of destination country







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